

MOSFET – Small Signal, Complementary, SC-88

30 V/-20 V, +0.25/-0.88 A

NTJD4158C, NVJD4158C

Features

- Leading 20 V Trench for Low $R_{DS(on)}$ Performance
- ESD Protected Gate
- SC-88 Package for Small Footprint (2 x 2 mm)
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Conversion
- Load/Power Management
- Load Switch
- Cell Phones, MP3s, Digital Cameras, PDAs

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage	N-Ch	V_{DS}	30	V
	P-Ch		-20	
Gate-to-Source Voltage	N-Ch	V_{GS}	± 20	V
	P-Ch		± 12	
N-Channel Continuous Drain Current (Note 1)	Steady State	I_D	$T_A = 25^\circ\text{C}$	A
			$T_A = 85^\circ\text{C}$	
P-Channel Continuous Drain Current (Note 1)	Steady State		$T_A = 25^\circ\text{C}$	A
			$T_A = 85^\circ\text{C}$	
Power Dissipation (Note 1)	Steady State	P_D	$T_A = 25^\circ\text{C}$	W
Pulsed Drain Current	N-Ch	I_{DM}	$t_p = 10\ \mu\text{s}$	A
	P-Ch			
Operating Junction and Storage Temperature		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)	N-Ch	I_S	0.25	A
	P-Ch		-0.48	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

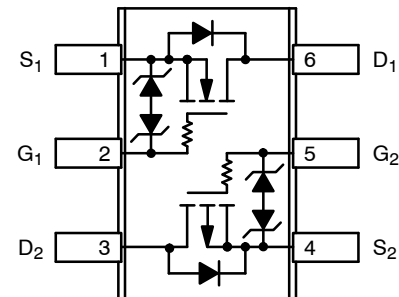
Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	460	$^\circ\text{C/W}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

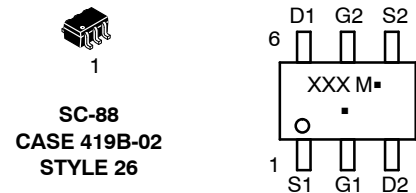
$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
N-Ch 30 V	1.0 Ω @ 4.5 V	0.25 A
	1.5 Ω @ 2.5 V	
P-Ch -20 V	215 m Ω @ -4.5 V	-0.88 A
	345 m Ω @ -2.5 V	

SC-88 (SOT-363)
(6-Leads)



(Top View)

MARKING DIAGRAM & PIN ASSIGNMENT



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 5.

NTJD4158C, NVJD4158C

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS (Note 3)							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	N	V _{GS} = 0 V	I _D = 250 μA	30		V
		P		I _D = -250 μA	-20		
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	N			33		mV/°C
		P			-9.0		
Zero Gate Voltage Drain Current	I _{DSS}	N	V _{GS} = 0 V, V _{DS} = 30 V	T _J = 25 °C		1.0	μA
		P	V _{GS} = 0 V, V _{DS} = -16 V			1.0	
		N	V _{GS} = 0 V, V _{DS} = 30 V	T _J = 125 °C	0.5		
		P	V _{GS} = 0 V, V _{DS} = -16 V		0.5		
Gate-to-Source Leakage Current	I _{GSS}	N	V _{DS} = 0 V, V _{GS} = 10 V			1.0	μA
		P	V _{DS} = 0 V, V _{GS} = -4.5 V			1.0	

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	N	V _{GS} = V _{DS}	I _D = 100 μA	0.8	1.2	1.5	V
		P		I _D = -250 μA	-0.45	-0.61	-1.5	
Negative Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J	N				3.2		mV/°C
		P				-2.7		
Drain-to-Source On Resistance	R _{DS(on)}	N	V _{GS} = 4.5 V, I _D = 10 mA		1.0	1.5		Ω
		P	V _{GS} = -4.5 V, I _D = -0.88 A		0.215	0.260		
		N	V _{GS} = 2.5 V, I _D = 10 mA		1.5	2.5		
		P	V _{GS} = -2.5 V, I _D = -0.71 A		0.345	0.500		
Forward Transconductance	g _{FS}	N	V _{DS} = 3.0 V, I _D = 10 mA		0.08			S
		P	V _{DS} = -10 V, I _D = -0.88 A		3.0			

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	N	f = 1 MHz, V _{GS} = 0 V	V _{DS} = 5.0 V		20	33	pF
		P		V _{DS} = -20 V		155	225	
Output Capacitance	C _{OSS}	N		V _{DS} = 5.0 V		19	32	
		P		V _{DS} = -20 V		25	40	
Reverse Transfer Capacitance	C _{RSS}	N		V _{DS} = 5.0 V		7.25	12	
		P		V _{DS} = -20 V		18	30	
Total Gate Charge	Q _{G(TOT)}	N		V _{GS} = 5.0 V, V _{DS} = 24 V, I _D = 0.1 A		0.9	1.5	nC
		P		V _{GS} = -4.5 V, V _{DS} = -10 V, I _D = -0.88 A		2.2	3.5	
Threshold Gate Charge	Q _{G(TH)}	N		V _{GS} = 5.0 V, V _{DS} = 24 V, I _D = 0.1 A		0.2		
		P		V _{GS} = -4.5 V, V _{DS} = -10 V, I _D = -0.88 A		0.2		
Gate-to-Source Charge	Q _{GS}	N		V _{GS} = 5.0 V, V _{DS} = 24 V, I _D = 0.1 A		0.3		
		P		V _{GS} = -4.5 V, V _{DS} = -10 V, I _D = -0.88 A		0.5		
Gate-to-Drain Charge	Q _{GD}	N		V _{GS} = 5.0 V, V _{DS} = 24 V, I _D = 0.1 A		0.2		
		P		V _{GS} = -4.5 V, V _{DS} = -10 V, I _D = -0.88 A		0.65		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	N	V _{GS} = 4.5 V, V _{DD} = 5.0 V, I _D = 250 mA, R _G = 50 Ω		15		ns
Rise Time	t _r				66		
Turn-Off Delay Time	t _{d(OFF)}				56		
Fall Time	t _f				78		
Turn-On Delay Time	t _{d(ON)}	P	V _{GS} = -4.5 V, V _{DD} = -10 V, I _D = -0.5 A, R _G = 20 Ω		5.8		
Rise Time	t _r				6.5		
Turn-Off Delay Time	t _{d(OFF)}				13.5		
Fall Time	t _f				3.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	N	V _{GS} = 0 V, T _J = 25 °C	I _S = 10 mA		0.65	0.7	V
		P		I _S = -0.48 A		-0.8	-1.2	
		N	V _{GS} = 0 V, T _J = 125 °C	I _S = 10 mA		0.45		
		P		I _S = -0.48 A		-0.66		
Reverse Recovery Time	t _{RR}	N	V _{GS} = 0 V, dI _S /dI = 8.0 A/μs	I _S = 10 mA		12.4		ns
		P	V _{GS} = 0 V, dI _S /dI = 100 A/μs	I _S = -0.48 mA		10.6		

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL N-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

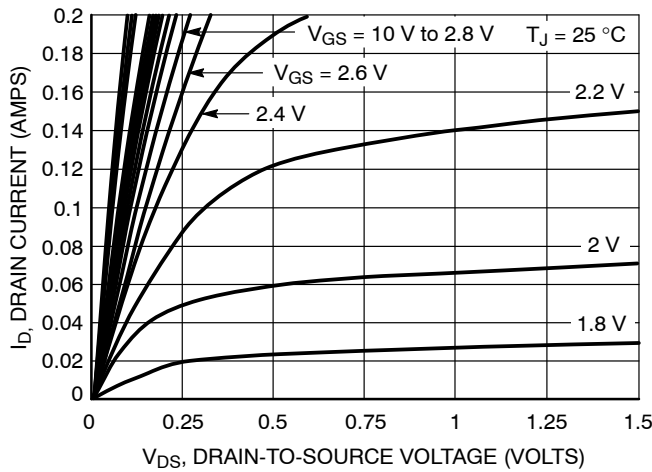


Figure 1. On-Region Characteristics

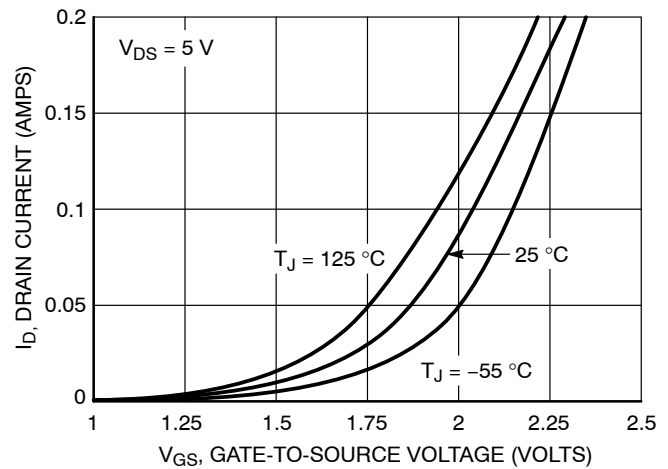


Figure 2. Transfer Characteristics

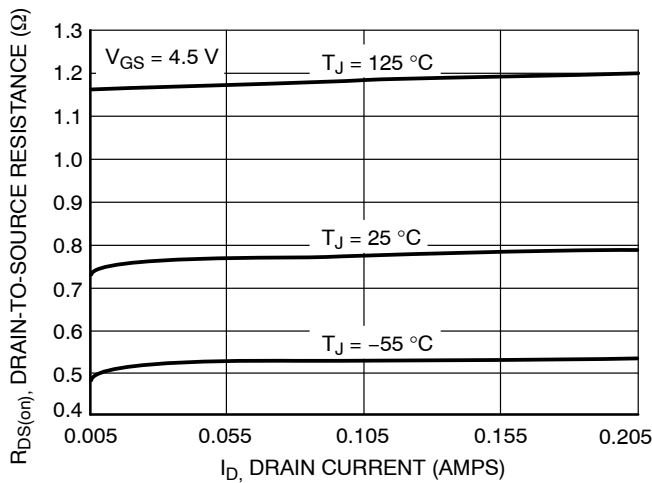


Figure 3. On-Resistance vs. Drain Current and Temperature

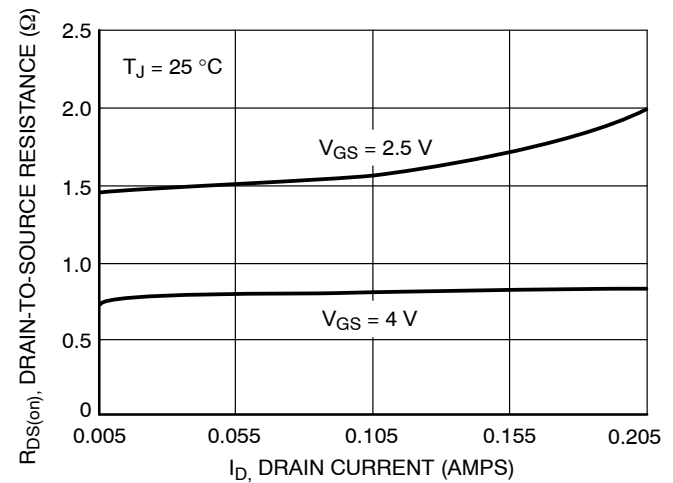


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

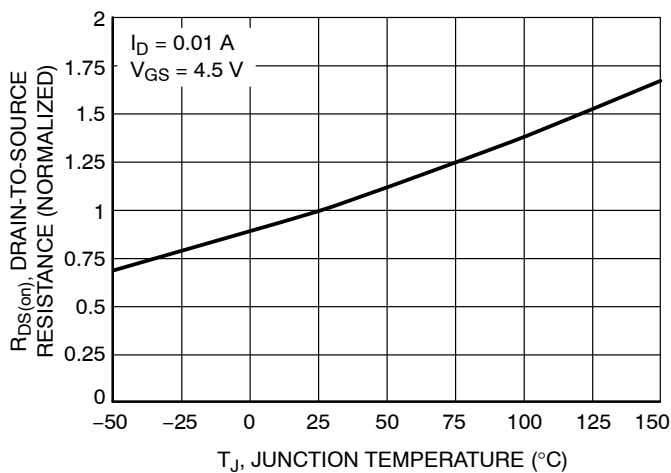


Figure 5. On-Resistance Variation with Temperature

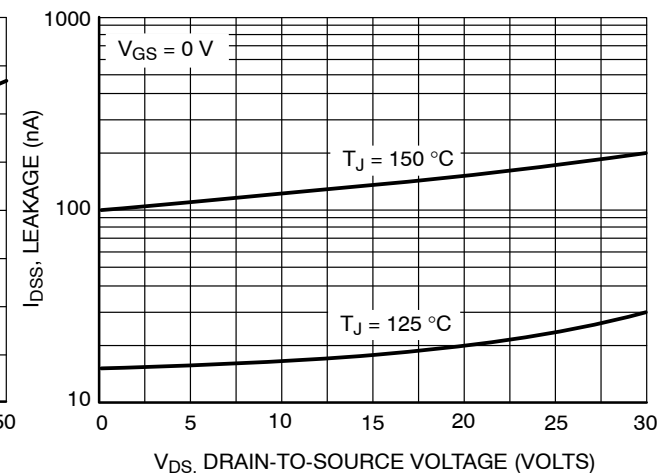


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL N-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

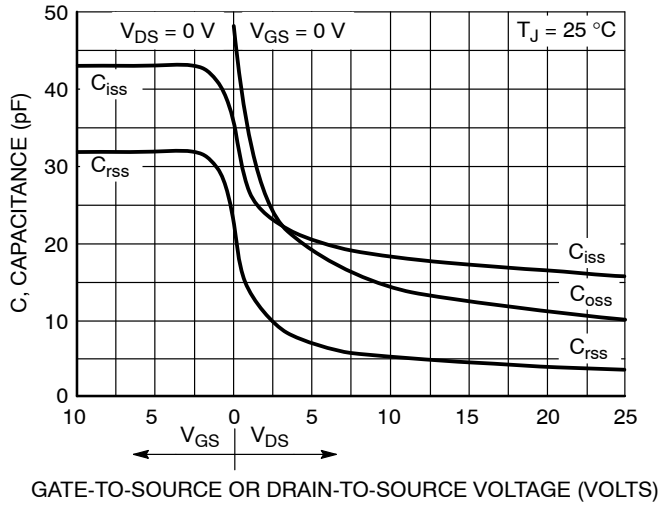


Figure 7. Capacitance Variation

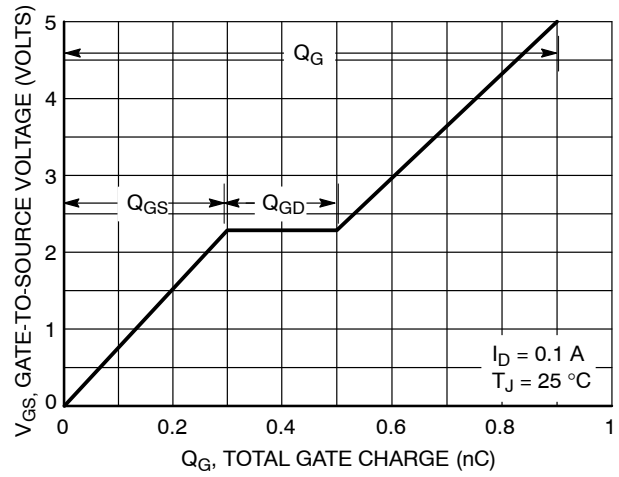


Figure 8. Gate-to-Source Voltage vs. Total Gate Charge

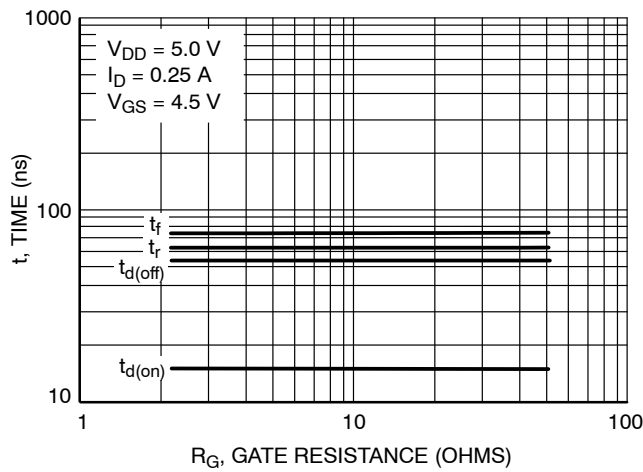


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

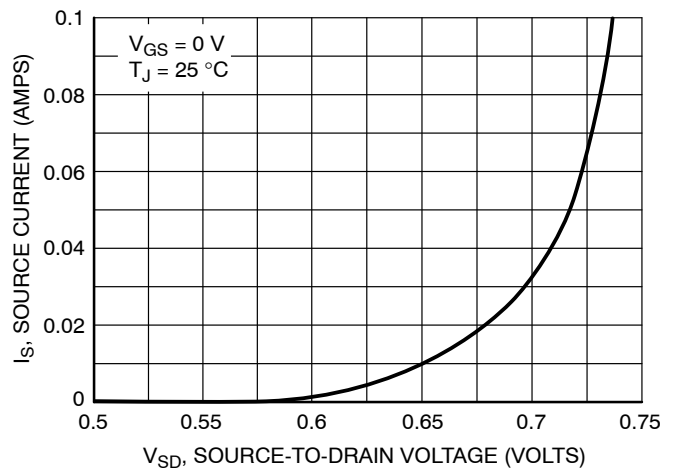


Figure 10. Diode Forward Voltage vs. Current

NTJD4158C, NVJD4158C

TYPICAL P-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

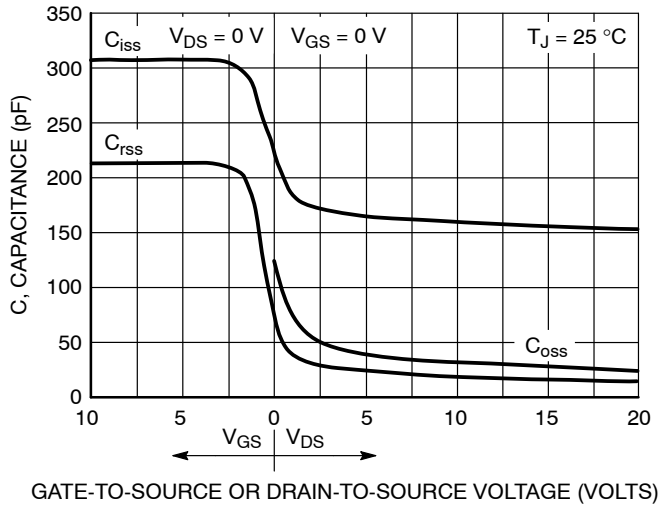


Figure 11. Capacitance Variation

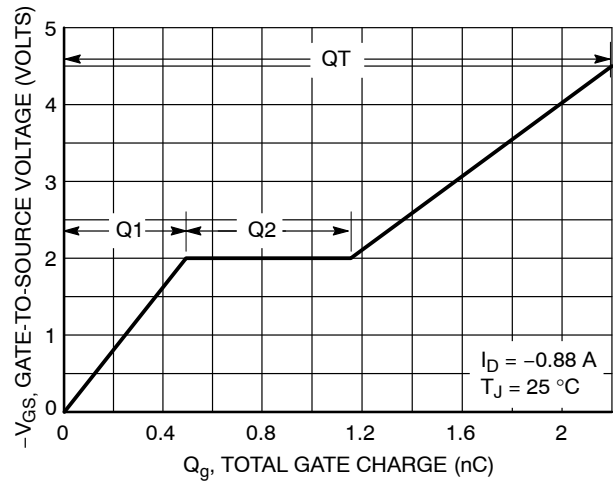


Figure 12. Gate-to-Source Voltage vs. Total Gate Charge

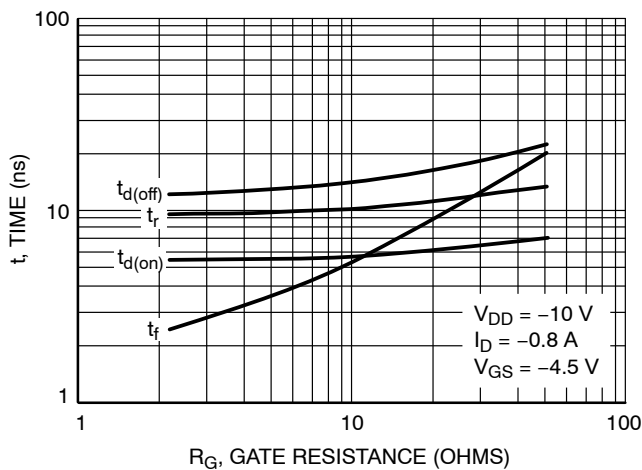


Figure 13. Resistive Switching Time Variation vs. Gate Resistance

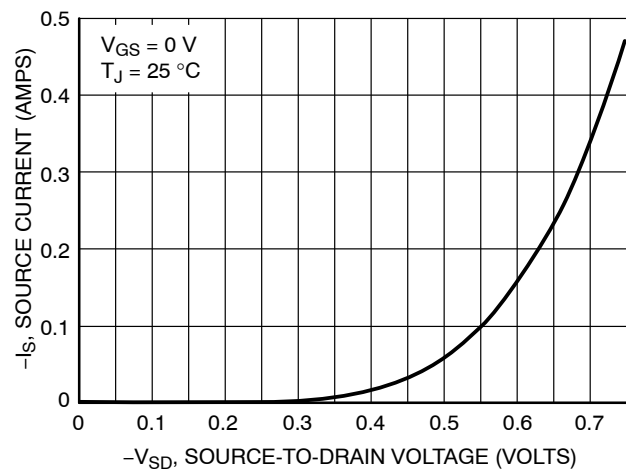


Figure 14. Diode Forward Voltage vs. Current

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTJD4158CT1G	TCD	SC-88 (Pb-Free)	3000 / Tape & Reel
NVJD4158CT1G*	VCD		

DISCONTINUED (Note 4)

NTJD4158CT2G	TCD	SC-88 (Pb-Free)	3000 / Tape & Reel
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[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

* NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

4. **DISCONTINUED:** This device is not available. Please contact your onsemi representative for information. The most current information on this device may be available on www.onsemi.com.

NTJD4158C, NVJD4158C

REVISION HISTORY

Revision	Description of Changes	Date
7	Document rebranded to onsemi format. NTJD4158CT2G OPN marked as discontinued.	1/13/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



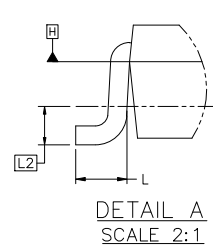
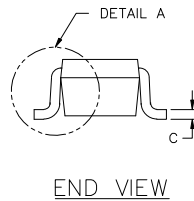
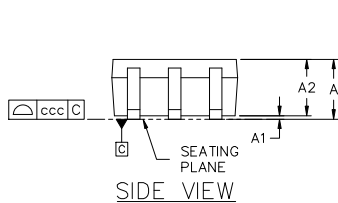
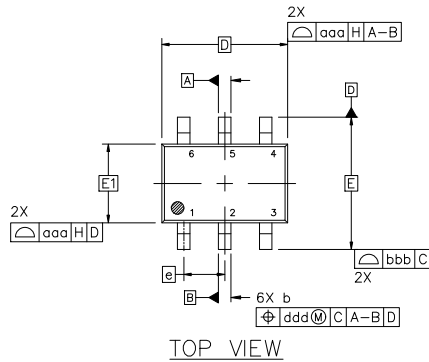


SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

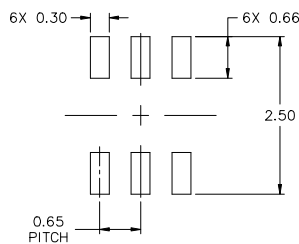
DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.



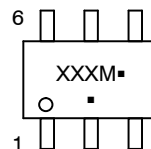
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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